

RF POWER FET

N-Channel Enhancement Mode

DESCRIPTION:

The **ASI MRF173** is Designed for wideband large-signal output and driver stages up to 200 MHz frequency range.

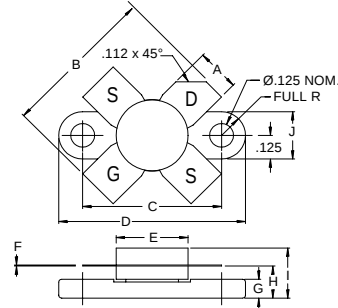
FEATURES:

- $P_G = 11$ dB Min. at 150 MHz
- **30:1 Load VSWR** Capability
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_D	9.0 A
V_{DSS}	65 V
V_{GS}	± 40 V
P_{DISS}	220 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	0.8 $^\circ\text{C/W}$

PACKAGE STYLE .500 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	$I_{DS} = 50$ mA	65			V
I_{DSS}	$V_{DS} = 28$ V $V_{GS} = 0$ V			2.0	mA
I_{GSS}	$V_{DS} = 0$ V $V_{GS} = 40$ V			1.0	μA
$V_{GS(th)}$	$I_D = 50$ mA $V_{DS} = 10$ V	1.0		6.0	V
g_{fs}	$I_D = 2.0$ A $V_{DS} = 10$ V	1.8	2.2		mho
C_{iss} C_{oss} C_{rss}	$V_{DS} = 28$ V $V_{GS} = 0$ V $f = 1.0$ MHz		110 105 10		pF
P_G η_D	$V_{DD} = 28$ V $I_{DQ} = 50$ mA $P_{out} = 80$ W $f = 150$ MHz	11 55	13 60		dB %
ψ	$V_{SWR} = 30:1$ AT ALL PHASE ANGLES	NO DEGRADATION IN OUTPUT POWER			

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